

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/559,979	12/08/2005	John Kouvetakis	05-720-US1	6573
20306 7	590 06/16/2006		EXAM	INER
MCDONNELL BOEHNEN HULBERT & BERGHOFF LLP			RAO, SHRINIVAS H	
300 S. WACKI 32ND FLOOR			ART UNIT	PAPER NUMBER
CHICAGO, IL			2814	
			DATE MAILED: 06/16/2000	5

Please find below and/or attached an Office communication concerning this application or proceeding.

			d
,*	Application No.	Applicant(s)	~
	10/559,979	KOUVETAKIS ET AL.	
Office Action Summary	Examiner	Art Unit	
	Steven H. Rao	2814	
The MAILING DATE of this communication ap Period for Reply	opears on the cover sheet w	ith the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPI WHICHEVER IS LONGER, FROM THE MAILING [- Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNI. .136(a). In no event, however, may a d will apply and will expire SIX (6) MO te, cause the application to become A	CATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 08 i	December 2005.		
<u> </u>	is action is non-final.		
3) Since this application is in condition for allow	ance except for formal mat	ters, prosecution as to the merits is	
closed in accordance with the practice under	Ex parte Quayle, 1935 C.I). 11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) <u>1-3</u> is/are pending in the application			
4a) Of the above claim(s) is/are withdra	awn from consideration.		
5) Claim(s) is/are allowed.			
6) Claim(s) <u>1-3</u> is/are rejected.			
7) Claim(s) is/are objected to.	/lkik		
8) Claim(s) are subject to restriction and/	or election requirement.		
Application Papers			
9)☐ The specification is objected to by the Examir			
10)⊠ The drawing(s) filed on <u>08 December 2005</u> is			
Applicant may not request that any objection to the			
Replacement drawing sheet(s) including the corre			
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreig	un priority under 35 LLS C	8 119(a)_(d) or (f)	
a) ☐ All b) ☐ Some * c) ☐ None of:	in priority under 55 0.5.C.	g 113(a)-(u) or (1).	
1. Certified copies of the priority documer	nts have been received.		
2. Certified copies of the priority documer		Application No	
3. Copies of the certified copies of the pri	ority documents have been	າ received in this National Stage	
application from the International Bure	au (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a lis	st of the certified copies no	t received.	
Attachment(s)			
1) Notice of References Cited (PTO-892)		Summary (PTO-413)	
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 		(s)/Mail Date Informal Patent Application (PTO-152)	
Paper No(s)/Mail Date	6) Other:		

Application/Control Number: 10/559,979

Art Unit: 2814

DETAILED ACTION

Priority

Acknowledgement is made of claim to priority from Provisional Patent Application No. 60/478,480 filed on June 13, 2003.

Therefore currently the earliest available filling date is June 13, 2003.

Information Disclosure Statement

To date no IDS has been filed in this case.

Double Patenting

Claims 1-2 are rejected under 35 U.S.C. 101 as claiming the same invention as that of claims 1-12 of prior U.S. Patent No. 6,897,471('471) This is a double patenting rejection.

Claim1 of the instant Application claims (a) substrate – also recited in claim 1 (a) of '471 patent as silicon substrate; (b) a Sn_x Ge _{1-x} layer on the substrate also recited in claim 1 (b) of '471 patent as Ge _{1-y} Sn_y and (c) Ge-Sn-Si layer over Sn_x Ge _{1-x} layer also recited in claim 1 (b) of '471 patent as Ge _{1-y-z}Sn_y Si_z.

Claim 2 of the instant Application claims the substrate as comprising silicon – also recited in claim 1 (a) of '471 patent as silicon substrate.

Claim 3 is rejected under 35 U.S.C. 101 as claiming the same invention as that of claims 1-19 of prior U.S. Patent No. 6,911,084 ('084) This is a double patenting rejection.

Claim 3 of the instant Application claims a method for synthesizing a compound having the molecular formula H₃Si-GeH₃ (claims 1, 15 and 16 of "084 patent) the method comprising combining H₃SiO₃SCF with KGEH₃ under conditions whereby H₃SiGeH₃ is obtained. (claims 1,15 and 16 of "084 patent).

The basis of double patenting rejections are (a) at least one common inventor and also (b) Subject to joint research agreement under 35USC 103 (c) (2) and 3 (Create Act), MPEP 804.03 etc.

There may be potential provisional double patenting issues over PCT/US04/43854 and PCT/US05/12157, if and when these applications reach national stage, also.

It is further noted that "471 patent (6,897,471) patent itself has a terminal disclaimer based on US patent No. 5,548,128.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- A. Claims 1-2 are rejected under 35 U.S.C. 102(b) as being anticipated by Soref et al. (U.S. Patent No. 5,548,128, hereinafter Soref).

With respect to claim 1 Soref describes a semiconductor structure comprising : a substrate (Soref figs. 1 or 2 # 1) , a SnxGel-x layer formed over the substrate(soref figs. 1 or 2 #13 , col. 2 line 45-47) and a Ge-Sn-Si layer formed over the SnxGel-x layer(Soref figs. 1 or 2 # 19, col. 3 line 44-45).

With respect to claim 2 Soref describes the semiconductor structure of claim 1 wherein the substrate comprises silicon. (Soref fig. 2 # 1, col. 2 lines 40-42).

B. Claim 3 is rejected under 35 U.S.C. 102(b) as being anticipated by Fiesalmann (U.S. Patent No. 4,777,023, herein after Fieselmann).

With respect to claim 3 Fiesalmann describes a method for synthesizing a compound having the molecular formula H3Si-GeH3 (Fieselman Exs. 1 to 7, etc.), the method comprising combining H3SiO3SCF3 with KGeH3 under conditions whereby H3SiGeH3 is obtained. (col.2 lines 37 to 46).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (571)272-1718. The examiner can normally be reached on 8.00 to 5.00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Fahmy Wael can be reached on (571) 272-1714. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 10/559,979

Art Unit: 2814

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Steven H. Rao

Patent Examiner

June 06, 2006.

LONG PHAM
PRIMARY EXAMINER